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The RF Line

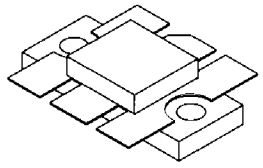
NPN Silicon RF Power Transistor

. . . designed primarily for wideband large–signal output and driver amplifier stages in the 100 to 500 MHz frequency range.

- Specified 28 Volt, 400 MHz Characteristics —
  Output Power = 100 Watts
  Minimum Gain = 7.0 dB
  Efficiency = 50% (Min)
- Built–In Matching Network for Broadband Operation Using Double Match Technique
- 100% Tested for Load Mismatch at all Phase Angles with 3:1 VSWR
- Gold Metallization System for High Reliability

MRF329

**100 W, 100 to 500 MHz
CONTROLLED "Q"
BROADBAND RF POWER
TRANSISTOR
NPN SILICON**



CASE 333–04, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	30	Vdc
Collector–Base Voltage	V_{CBO}	60	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous — Peak	I_C	9.0 12	Adc
Total Device Dissipation @ T_C = 25°C (1) Derate above 25°C	P_D	270 1.54	Watts W/°C
Storage Temperature Range	T_{stg}	–65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{\theta JC}$	0.65	°C/W

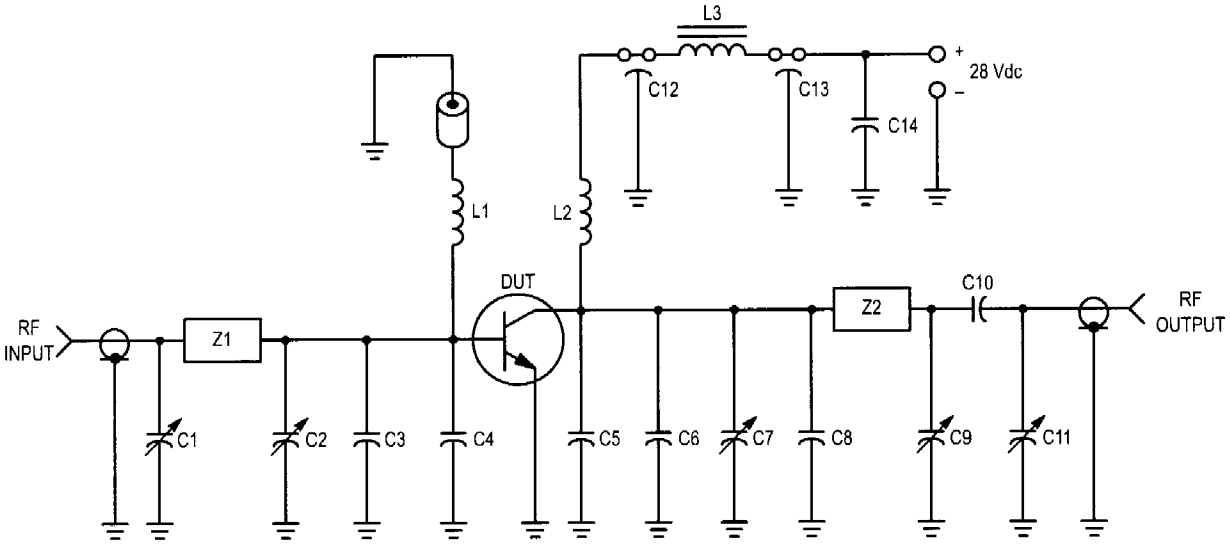
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 80 mAdc, I_B = 0)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector–Emitter Breakdown Voltage (I_C = 80 mAdc, V_{BE} = 0)	$V_{(BR)CES}$	60	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 8.0 mAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	—	—	Vdc

NOTES: (continued)
1. This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.
2. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

ELECTRICAL CHARACTERISTICS — continued (T_C = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS (continued)					
Collector–Base Breakdown Voltage (I_C = 80 mAdc, I_E = 0)	$V_{(BR)CBO}$	60	—	—	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	—	—	5.0	mAdc
ON CHARACTERISTICS					
DC Current Gain (I_C = 4.0 Adc, V_{CE} = 5.0 Vdc)	h_{FE}	20	—	80	—
DYNAMIC CHARACTERISTICS					
Output Capacitance (V_{CB} = 28 Vdc, I_E = 0, f = 1.0 MHz)	C_{ob}	—	95	125	pF
FUNCTIONAL TESTS (Figure 1)					
Common–Emitter Amplifier Power Gain (V_{CC} = 28 Vdc, P_{out} = 100 W, f = 400 MHz)	G_{PE}	7.0	9.7	—	dB
Collector Efficiency (V_{CC} = 28 Vdc, P_{out} = 100 W, f = 400 MHz)	η	50	60	—	%
Load Mismatch (V_{CC} = 28 Vdc, P_{out} = 100 W, f = 400 MHz, VSWR = 3:1 all angles)	ψ	No Degradation in Output Power			



C1, C2, C7, C9 — 1.0–20 pF Johanson (JMC 5501)
C3, C4 — 36 pF 100 mil Chip Cap (ATC)
C5, C6 — 50 pF 100 mil Chip Cap (ATC)
C8 — 30 pF 100 mil Chip Cap (ATC)
C10 — 2.0–150 pF 100 mil Chip Caps in Parallel (ATC)
C11 — 1.0–10 pF Johanson (JMC 5201)
C12, C13 — 1000 pF UNELCO Feedthru
C14 — 0.1 μF Erie Redcap

L1 — 0.15 μH Molded Choke with Ferrite Bead (Ferroxcube #56–590–65/4B) on Ground End
L2 — 4 Turns #18 AWG, 1/4″ ID
L3 — Ferroxcube VK200–19/4B

Z1 — Microstrip Line 2300 mils L x 210 mils W
Z2 — Microstrip Line 2300 mils L x 280 mils W

Board — Glass Teflon, t = 0.062″, ε_r = 2.56

Figure 1. 400 MHz Test Circuit